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PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants:

Aizenberg et al.

Serial No.:

10/722,613

Filed:

November 26, 2003

For:

DEVICES HAVING PATTERNED REGIONS OF POLYCRYSTALLINE ORGANIC SEMICONDUCTORS, AND METHODS OF MAKING THE SAME

Group:

2811

Examiner:

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on the date set forth below:

Signed:

Name: Marianna Tortorelli

Date: June 14, 2004

Durham, North Carolina June 14, 2004

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INFORMATION DISCLOSURE STATEMENT UNDER § 197(a)

Sir:

This Information Disclosure Statement is being filed before a first Official Action has been mailed in this case.

Pursuant to 37 C.F.R. 1.56, 1.97 and 1.98, applicant's attorney wishes to bring to the attention of the Patent and Trademark Office the following items listed on the accompanying Forms PTO/SB/08A and PTO/SB/08B.

ITEMS

	Document No.	<u>Publication</u>	Patentee/Applicant
1.	U.S. Patent No. 5,192,580	<u>Date</u> 03/09/1993	Blanchet-Fincher
2.	U.S. Patent No. 5,288,528	02/22/1994	Blanchet-Fincher
3.	U.S. Patent No. 5,347,144	09/13/1994	Garnier et al.
4.	U.S. Patent No. 5,523,192	06/04/1996	Blanchet-Fincher
5.	U.S. Patent No. 5,563,019	10/08/1996	Blanchet-Fincher
6.	U.S. Patent No. 5,625,199	04/29/1997	Baumbach et al.
7.	U.S. Patent No. 5,766,819	06/16/1998	Blanchet-Fincher
8.	U.S. Patent No. 5,840,463	11/24/1998	Blanchet-Fincher
9.	U.S. Patent No. 5,981,970	11/09/1999	Dimitrakopoulos et al.
10.	U.S. Patent No. 6,051,318	04/18/2000	Kwon
11.	U.S. Patent No. 6,143,451	11/07/2000	Blanchet-Fincher
12.	U.S. Patent No. 6,146,792	11/14/2000	Blanchet-Fincher et al.
13.	U.S. Patent No. 6,174,651	01/16/2001	Thakur
14.	U.S. Patent No. 6,265,243	07/24/2001	Katz et al.
15.	U.S. Patent No. 6,352,811	03/05/2002	Patel et al.
16.	U.S. Patent No. 6,352,812	03/05/2002	Shimazu et al.
17.	U.S. Patent No. 6,403,397	06/11/2002	Katz
18.	U.S. Patent No. 6,551,717	04/22/2003	Katz et al.
19.	U.S. Publication No. 2002/0149315 A1	10/17/2002	Blanchet-Fincher
20.	U.S. Application No. 10/256,885	09/27/2002	Bao et al.
21.	U.S. Application No. 10/669,780	09/24/2003	Bao

22.	U.S. Application No. 60/505,533	09/24/2003	Meth
23.	U.S. Application No. 60/505,880	09/24/2003	Meth et al.
24.	U.S. Application No. 10/671,303	09/24/2003	Bao et al.
25.	U.S. Application No. 10/701/183	11/04/2003	Akkerman et al.
26.	PCT Publication No. WO 01/87634 A2	11/22/2001	E.I. du Pont de Nemours and Company
27.	PCT Publication No. WO 02/08801 A1	01/31/2002	E.I. du Pont de Nemours and Company
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- 29. AFZALI ET AL., High-Performance, Solution-Processed Organic Thin Film Transistors from a Novel Pentacene Precursor, J. Am. Chem. Soc., 2002, Page(s) 8812-8813, Volume 124
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The filing of this Information Disclosure Statement shall not be construed as a representation that a search has been made nor shall it be construed as an admission that the

information cited is considered to be material to patentability, nor shall it be construed that no other material information exists.

Respectfully submitted,

Jay M. Brown

Reg. No. 30,033

Priest & Goldstein, PLLC 5015 Southpark Drive, Suite 230

Durham, NC 27713-7736

(919) 806-1600

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	substitute for form 1449A/PTO			Complete if Known		
	absulate for form 1443747 10			Application Number	10/722,613	
	INFORMATION DISC	LOS	URE	Filing Date	November 26, 2003	
	STATEMENT BY APP	LIC	ANT	First Named Inventor	Aizenberg et al.	
	(Use as many sheets as nece	ssary)		Art Unit	2811	
				Examiner Name		
Sheet	1	of	5	Attorney Docket Number	100.2496	

			U.S. PATENT	DOCUMENTS	
Examiner Initials*	Cite No.1	Document Number Number - Kind Code ^{2 (if known)}	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	1	US- 5,192,580	03/09/1993	Blanchet-Fincher	
	2	US- 5,288,528	02/22/1994	Blanchet-Fincher	
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	20	US- 10/256,885	09/27/2002	Bao et al.	

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110.	Country Code - Number - Kind Code (if known)			or Relevant Figures Appear	\vdash	
		Foreign Patent Document Cite	Cite Foreign Patent Document Publication Date	Cite Publication Date Name of Patentee or	Foreign Patent Document Publication Date Name of Patentee or Where Relevant Passages AMA DD YYYY Applicant of Cited Document Where Relevant Passages	

Examiner	Date
Signature	Considered

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Su	Substitute for form 1449A/PTO			Application Number	10/722,613
	NEODMATION DISCL	OSI	IDE	Filing Date	November 26, 2003
-	INFORMATION DISCLOSURE		First Named Inventor	Aizenberg et al.	
	STATEMENT BY APP	LICA	ANT	Art Unit	2811
	(Use as many sheets as necessary)		Examiner Name		
Sheet	2		5	Attorney Docket Number	100.2496

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	26	WO 01/87634 A2	11/22/2001	E.I. du Pont de Nemours and Company				
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		NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
mudio	29	AFZALI ET AL., High-Performance, Solution-Processed Organic Thin Film Transistors from a Novel Pentacene Precursor, J. Am. Chem. Soc., 2002, Page(s) 8812-8813, Volume 124	
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	41	FORREST, Ultrathin Organic Films Grown by Organic Molecular Beam Deposition and Related Techniques, Chem. Rev., Page(s) 1793-1896, Volume 97, Publisher: American Chemical Society	
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4-19-19-19-19-19-19-19-19-19-19-19-19-19-	46	JOHNSTON ET AL., Low-Energy Vibrational Modes in Phenylene Oligomers Studied by THz Time-Domain Spectroscopy, Chemical Physics Letters, 2003, Page(s) 256-262, Volume 377	
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INF	ORMATION DISC	CLOSU	IRE	Filing Date	November 26, 2003
STA	STATEMENT BY APPLICANT			First Named Inventor	Aizenberg et al.
0				Art Unit	2811
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	54	SEO ET AL., Interpretation of the Mass Change Behavior in the Binary Monolayer of Hydroquinone-tethered Alkylthiol and Aminoalkythiol, Bull. Korean Chem. Soc., 2002, Page(s) 1671-1673, Volume 23, Number 11			
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